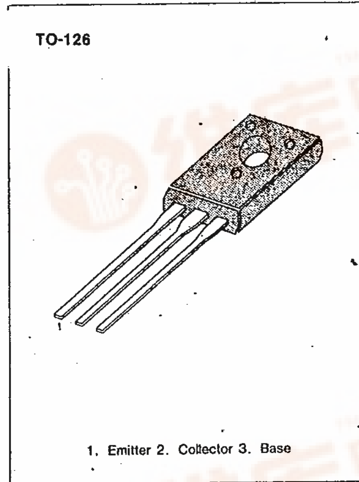
查询MJE702供应商 捷多邦，专业PCB打样工厂，24小时加急出货

MJE700/701/702/703 NPN EPITAXIAL SILICON DARLINGTON TRANSISTOR

T-33-31

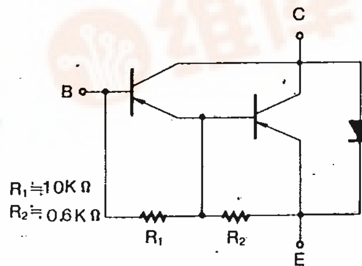
HIGH DC CURRENT GAIN
MIN h_{FE}=750 @ I_C=−1.5 and −2.0A DC
MONOLITHIC CONSTRUCTION WITH BUILT-IN BASE-EMITTER RESISTORS

- Complementary to MJE800/801/802/803



ABSOLUTE MAXIMUM RATINGS (T_a=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}		
:MJE700/701		−60	V
:MJE702/703		−80	V
Collector-Emitter Voltage	V_{CEO}		
:MJE700/701		−60	V
:MJE702/703		−80	V
Emitter-Base Voltage	V_{EBO}	−5	V
Collector Current	I_C	−4	A
Base Current	I_B	−0.1	A
Collector Dissipation	P_C	40	W
Junction Temperature	T_j	150	°C
Storage Temperature	Tstg	−55~150	°C



ELECTRICAL CHARACTERISTICS (T_a=25°C)

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector Emitter Breakdown Voltage	BV_{CEO}				
:MJE700/701		I_C=−50mA, I_B=0	−60		V
:MJE702/703			−80		V
Collector Cutoff Current	I_{CEO}				
:MJE700/701		V_{CE}=−60V, I_B=0		−100	μA
:MJE702/703		V_{CE}=−80V, I_B=0		−100	μA
Collector Cutoff Current	I_{CBO}	V_{CB}=Rated BV_{CEO}, I_E=0		−100	μA
		V_{CB}=Rated BV_{CEO}, I_E=0 T_C=100°C		−500	μA
Emitter Cutoff Current	I_{EBO}	V_{BE}=−5V, I_C=0		−2	mA
DC Current Gain :MJE700/702	h_{FE}	V_{CE}=−3V, I_C=−1.5A	750		
:MJE701/703		V_{CE}=−3V, I_C=−2A	750		
:ALL DEVICES		V_{CE}=−3V, I_C=−4A	100		
Collector-Emitter Saturation Voltage:	V_{CE}(sat)				
:MJE700/702		I_C=−1.5A, I_B=−30mA		−2.5	V
:MJE701/703		I_C=−2A, I_B=−40mA		−2.8	V
:ALL DEVICES		I_C=−4A, I_B=−40mA		−3	V
Base-Emitter On Voltage	V_{BE}(on)				
:MJE700/702		V_{CE}=−3V, I_C=−1.5A		−2.5	V
:MJE701/703		V_{CE}=−3V, I_C=−2A		−2.5	V
:ALL DEVICES		V_{CE}=−3V, I_C=−4A		−3	V

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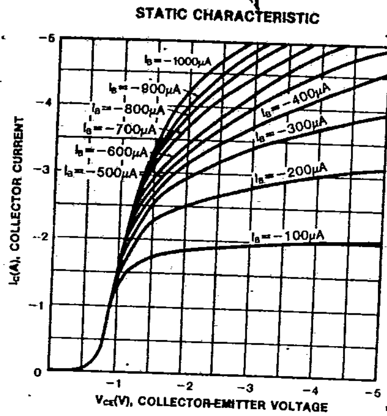
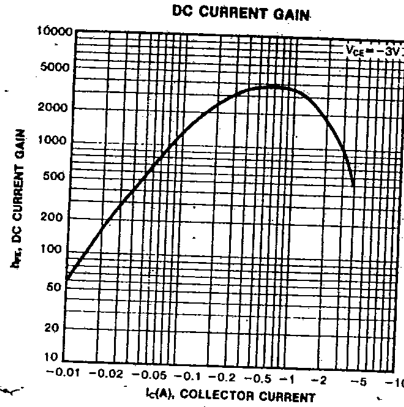
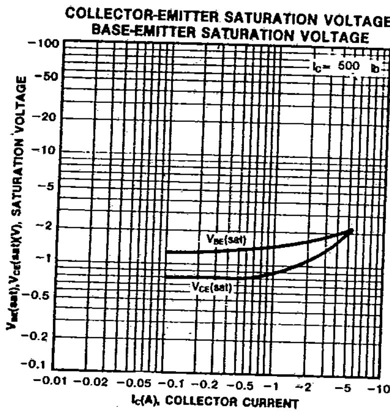
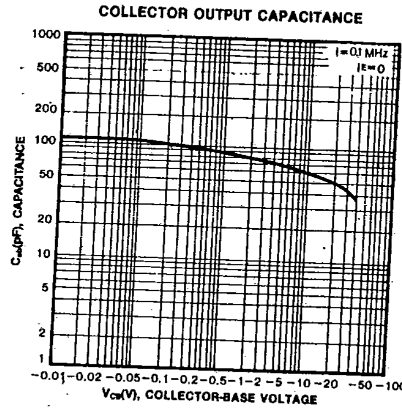
MJE700/701/702/703   NPN EPITAXIAL SILICON DARLINGTON TRANSISTOR

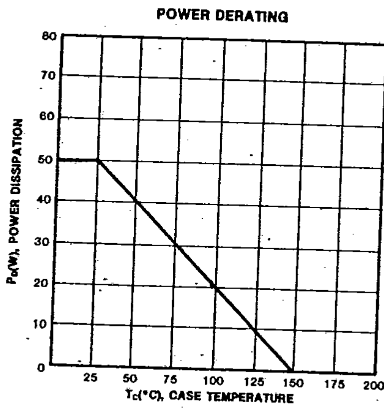
T-33-31

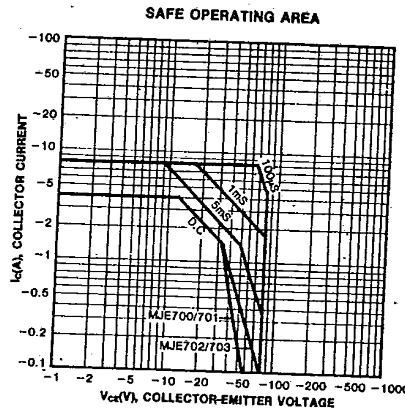








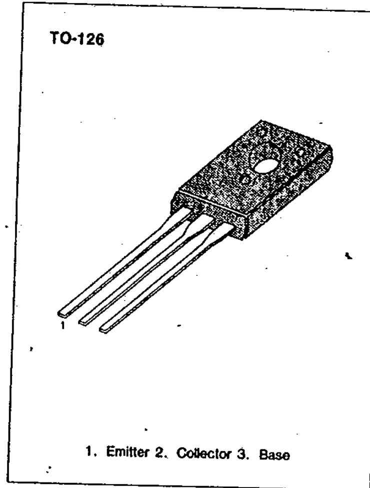




MJE800/801/802/803 NPN EPITAXIAL SILICON DARLINGTON TRANSISTOR

HIGH DC CURRENT GAIN
MIN h_{FE}=750 @ I_C=−1.5 and −2.0A DC
MONOLITHIC CONSTRUCTION WITH BUILT-IN BASE-EMITTER RESISTORS

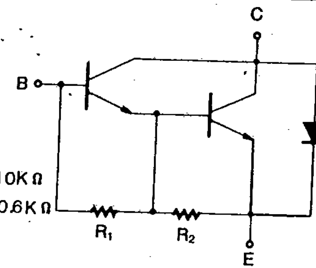
- Complementary to MJE700/701/702/703



1. Emitter 2. Collector 3. Base

ABSOLUTE MAXIMUM RATINGS (T_a=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}		
:MJE800/801		60	V
:MJE802/803		80	V
Collector-Emitter Voltage	V_{CEO}		
:MJE800/801		60	V
:MJE802/803		80	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	4	A
Base Current	I_B	0.1	A
Collector Dissipation	P_C	40	W
Junction Temperature	T_j	150	°C
Storage Temperature	Tstg	−55~150	°C



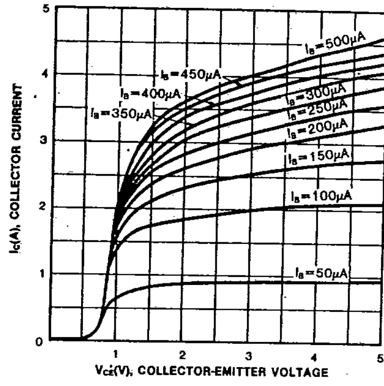
R_1≒10KΩ
R_2≒0.6KΩ

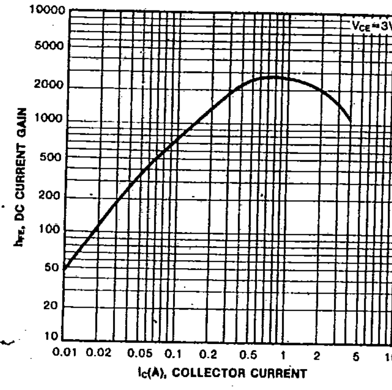
ELECTRICAL CHARACTERISTICS (T_a=25°C)

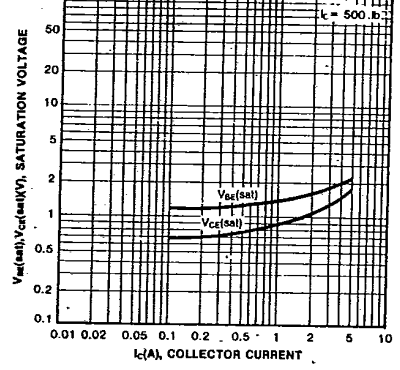
Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector Emitter Breakdown Voltage	BV_{CEO}				
:MJE800/801		I_C=50mA, I_B=0	60		V
:MJE802/803			80		V
Collector Cutoff Current	I_{CEO}				
:MJE800/801		V_{CE}=60V, I_B=0		100	μA
:MJE802/803		V_{CE}=80V, I_B=0		100	μA
Collector Cutoff Current	I_{CBO}	V_{CB}=Rated BV_{CEO}, I_E=0		100	μA
		V_{CB}=Rated BV_{CEO}, I_E=0, T_C=100°C		500	μA
Emitter Cutoff Current	I_{EBO}	V_{BE}=5V, I_C=0		2	mA
DC Current Gain :MJE800/802	h_{FE}	V_{CE}=3V, I_C=1.5A	750		
:MJE801/803		V_{CE}=3V, I_C=2A	750		
:ALL DEVICES		V_{CE}=3V, I_C=4A	100		
Collector-Emitter Saturation Voltage:	V_{CE}(sat)				
:MJE800/802		I_C=1.5A, I_B=30mA		2.5	V
:MJE801/803		I_C=2A, I_B=40mA		2.8	V
:ALL DEVICES		I_C=4A, I_B=40mA		3	V
Base-Emitter On Voltage	V_{BE}(on)				
:MJE800/802		V_{CE}=3V, I_C=1.5A		2.5	V
:MJE801/803		V_{CE}=3V, I_C=2A		2.5	V
:ALL DEVICES		V_{CE}=3V, I_C=4A		3	V

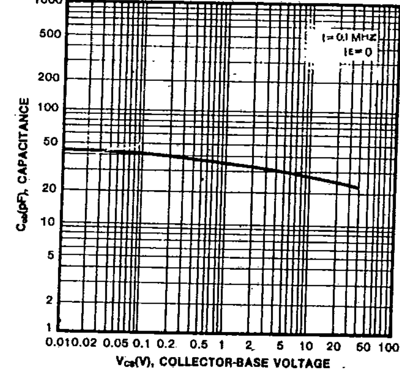
MJE800/801/802/803 NPN EPITAXIAL SILICON DARLINGTON TRANSISTOR

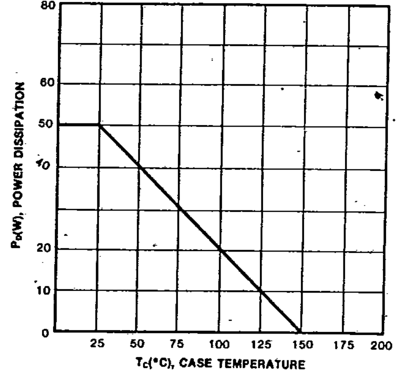
T-33-29

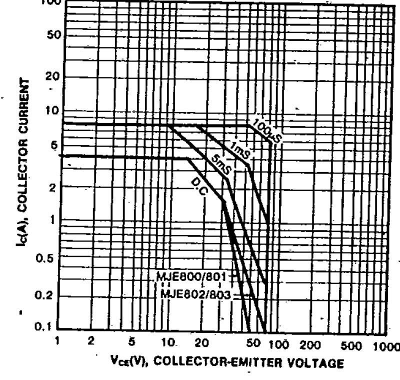












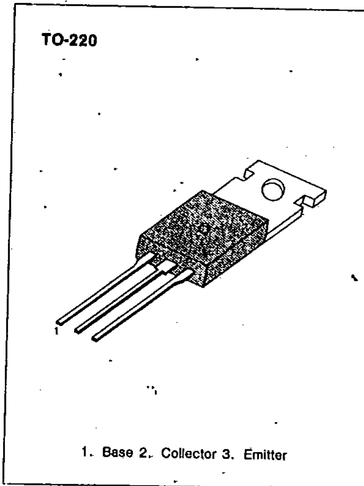
MJE2955T **PNP SILICON TRANSISTOR**

T-33-21

GENERAL PURPOSE AND SWITCHING APPLICATIONS
DC CURRENT GAIN SPECIFIED TO 10 AMPERES

- High Current Gain-Bandwidth Product (f_T=2MHz (MIN))

TO-220



1. Base 2. Collector 3. Emitter

ABSOLUTE MAXIMUM RATINGS (T_a=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	−70	V
Collector-Emitter Voltage	V_{CEO}	−60	V
Emitter-Base Voltage	V_{EBO}	−5	V
Collector Current	I_C	−10	A
Base Current	I_B	−6	A
Collector Dissipation (T_C=25°C)	P_C	75	W
Collector Dissipation (T_a=25°C)	P_C	0.6	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	−55~150	°C

ELECTRICAL CHARACTERISTICS (T_a=25°C)

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector Emitter Sustaining Voltage	V_{CEO}(sus)	I_C=−200mA, I_B=0	−60		V
Collector Cutoff Current	I_{CEO}	V_{CE}=−30V, I_B=0		−700	μA
Collector Cutoff Current	I_{CEX}	V_{CE}=−70V, V_{BE}(off)=1.5V		−1	mA
		V_{CE}=−70V, V_{BE}(off)=1.5V T_C=150°C		−5	mA
Emitter Cutoff Current	I_{EBO}	V_{EB}=−5V, I_C=0		−5	mA
*DC Current Gain	h_{FE}	V_{CE}=−4V, I_C=−4A	20	100	
		V_{CE}=−4V, I_C=−10A	5		
*Collector Emitter Saturation Voltage	V_{CE}(sat)	I_C=−4A, I_B=−0.4A		−1.1	V
		I_C=−10A, I_B=−3.3A		−8	V
*Base Emitter On Voltage	V_{BE}(on)	V_{CE}=−4V, I_C=−4A		−1.8	V
Current Gain Bandwidth Product	f_T	V_{CE}=−10V, I_C=−500mA, f=500KHz	2		MHz

* Pulse test: PW≤300μs, duty cycle≤2% Pulse

3

T-33-21